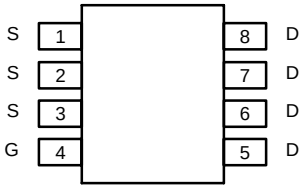
N-Channel Reducded Q_g, Fast Switching MOSFET

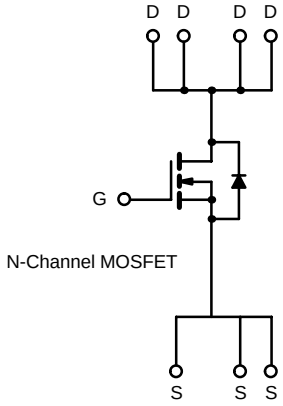
PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
30	0.0185 @ V_{GS} = 10 V	9
	0.033 @ V_{GS} = 4.5 V	7

TrenchFET® Power MOSFETs
High-Efficiency PWM Optimized

SO-8



Top View



N-Channel MOSFET

Ordering Information: Si4800DY
Si4800DY-T1 (with Tape and Reel)

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±25	
Continuous Drain Current (T_J = 150°C)[a, b]	T_A = 25°C	I_D	9	A
	T_A = 70°C		7	
Pulsed Drain Current (10 μs Pulse Width)		I_{DM}	40	
Continuous Source Current (Diode Conduction)[a, b]		I_S	2.3	
Maximum Power Dissipation[a, b]	T_A = 25°C	P_D	2.5	W
	T_A = 70°C		1.6	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient (MOSFET)[a]	t ≤ 10 sec	R_{thJA}		50	°C/W
	Steady State		70		

Notes
a. Surface Mounted on FR4 Board.
b. t ≤ 10 sec.

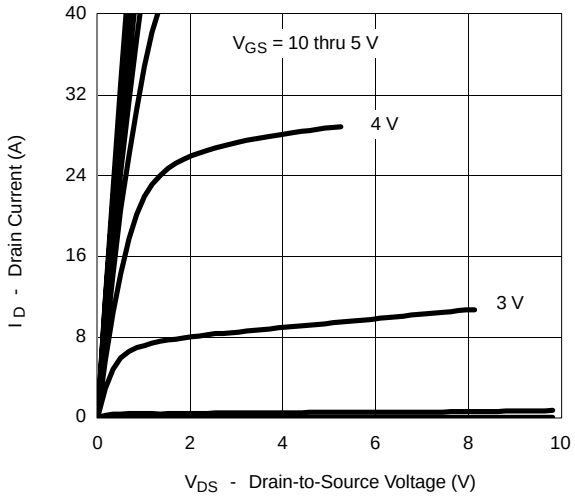
MOSFET SPECIFICATIONS (T_J = 25°C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 μA	0.8			V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 24 V, V_{GS} = 0 V			1	μA
		V_{DS} = 24 V, V_{GS} = 0 V, T_J = 55°C			5	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} ≥ 5 V, V_{GS} = 10 V	30			A
Drain-Source On-State Resistance[a]	$r_{DS(on)}$	V_{GS} = 10 V, I_D = 9 A		0.0155	0.0185	Ω
		V_{GS} = 4.5 V, I_D = 7 A		0.0275	0.033	
Forward Transconductance[a]	g_{fs}	V_{DS} = 15 V, I_D = 9 A		16		S
Diode Forward Voltage[a]	V_{SD}	I_S = 2.3 A, V_{GS} = 0 V		0.71	1.2	V
Dynamic[b]						
Total Gate Charge	Q_g	V_{DS} = 15 V, V_{GS} = 5.0 V, I_D = 9 A		8.7	13	nC
Gate-Source Charge	Q_{gs}			2.25		
Gate-Drain Charge	Q_{gd}			4.2		
Gate Resistance	R_g		0.5	1.5	2.6	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 15 V, R_L = 15 Ω I_D ≅ 1 A, V_{GEN} = 10 V, R_G = 6 Ω		11	16	ns
Rise Time	t_r			8	15	
Turn-Off Delay Time	$t_{d(off)}$			22	30	
Fall Time	t_f			9	15	
Source-Drain Reverse Recovery Time	t_{rr}	I_F = 2.3 A, di/dt = 100 A/μs		50	80	

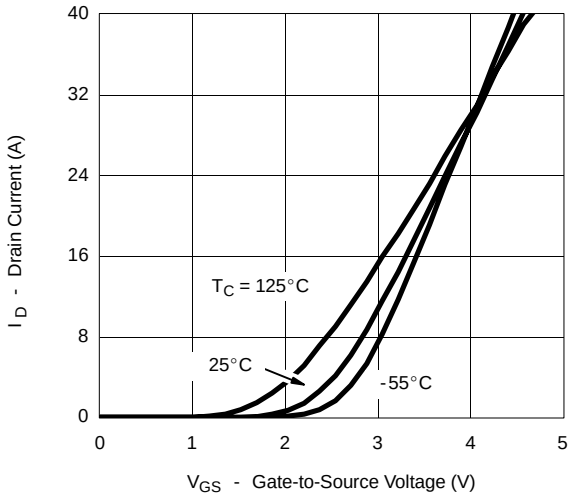
Notes
a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

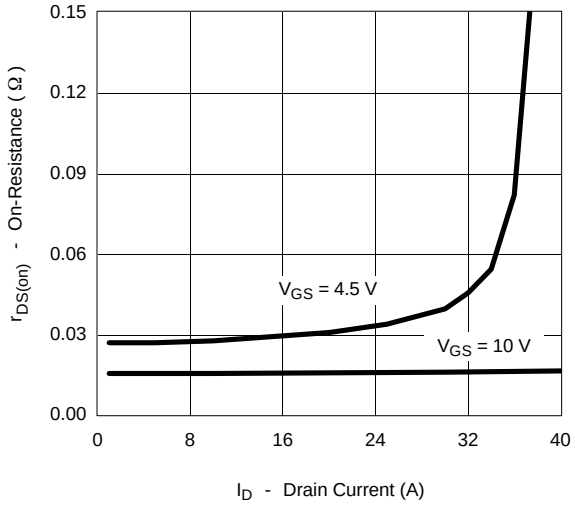
Output Characteristics



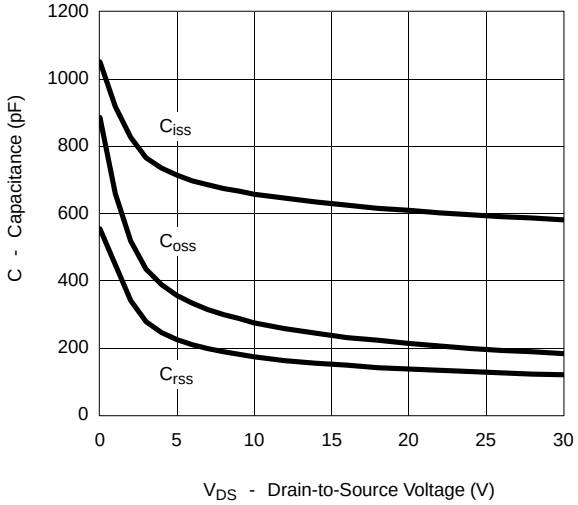
Transfer Characteristics



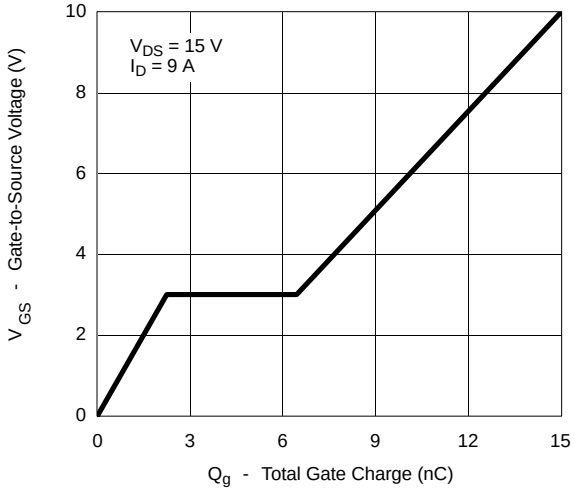
On-Resistance vs. Drain Current



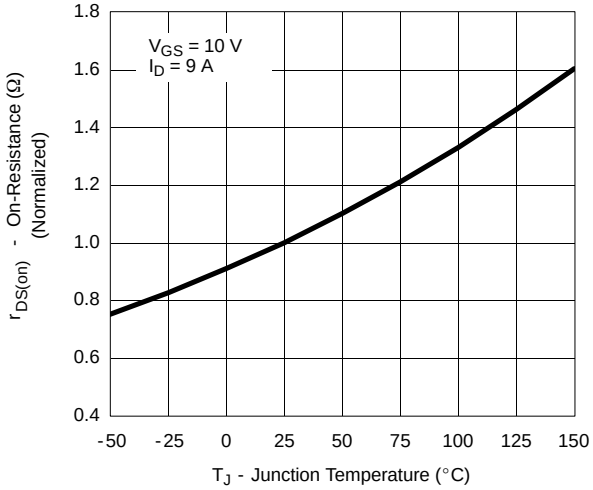
Capacitance



Gate Charge

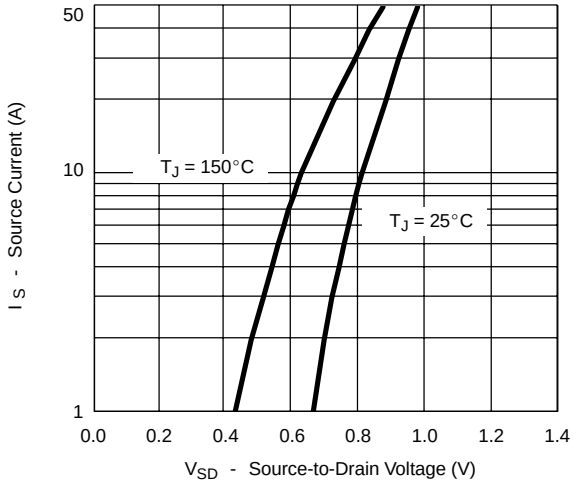


On-Resistance vs. Junction Temperature

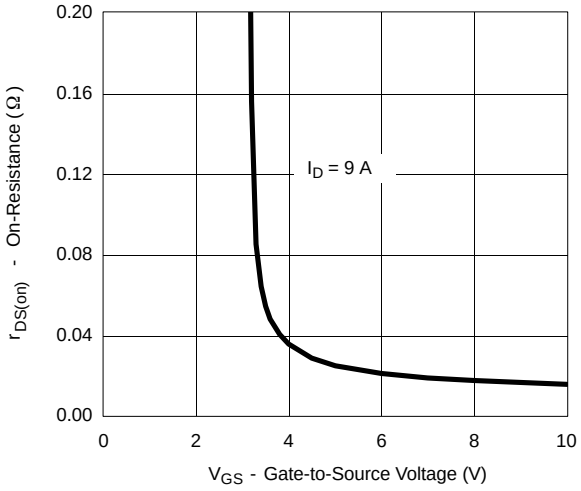


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

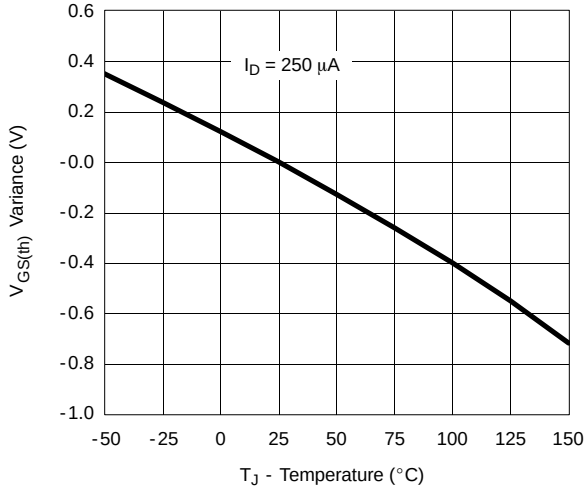
Source-Drain Diode Forward Voltage



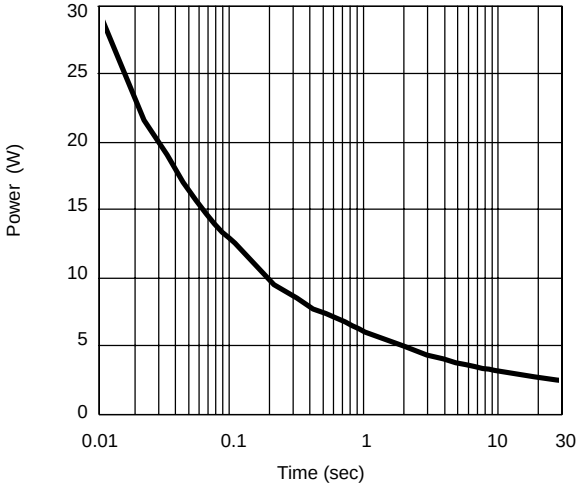
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient